

## **Schottky Barrier Rectifiers**

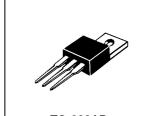
Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

- \* Low Forward Voltage.
- \* Low Switching noise.
- \* High Current Capacity
- \* Guarantee Reverse Avalanche.
- \* Guard-Ring for Stress Protection.
- \* Low Power Loss & High efficiency.
- \* 150 Operating Junction Temperature
- \*Low Stored Charge Majority Carrier Conduction.
- \* Plastic Material used Carries Underwriters Laboratory

Flammability Classification 94V-O

## SCHOTTKY BARRIER RECTIFIERS

30 AMPERES 100 VOLTS



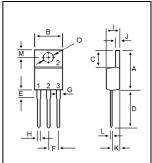
**TO-220AB** 

## **MAXIMUM RATINGS**

Characteristic	Symbol	S30C100C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	70	V
Average Rectifier Forward Current Total Device (Rated V <sub>R</sub> ), T <sub>C</sub> =100	I <sub>F(AV)</sub>	15 30	А
Peak Repetitive Forward Current (Rate V <sub>R</sub> , Square Wave, 20kHz)	I <sub>FM</sub>	30	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase, 60Hz)	I <sub>FSM</sub>	250	А
Operating and Storage Junction Temperature Range	$T_J,T_stg$	-65 to +150	

## **ELECTRIAL CHARACTERISTICS**

Characteristic	Symbol	S30C150C	Unit
Maximum Instantaneous Forward Voltage ( $I_F = 15 \text{ Amp } T_C = 25$ ) ( $I_F = 15 \text{ Amp } T_C = 125$ )	V <sub>F</sub>	0.95 0.85	V
Maximum Instantaneous Reverse Current ( Rated DC Voltage, $T_C = 25$ ) ( Rated DC Voltage, $T_C = 125$ )	I <sub>R</sub>	0.5 30	mA



DIM	MILLIMETERS	
DIIVI	MIN	MAX
Α	14.68	15.32
В	9.78	10.42
С	5.02	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	2.66
G	1.12	1.36
Н	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.98
L	0.33	0.55
M	2.48	2.98
0	3.70	3.90

